

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A semiconductor device fabricating method includes ~~an amorphous silicon laminating process for forming an amorphous silicon film (2) on a substrate (1), an irradiation process for irradiating the amorphous silicon film (2) with laser light (16) to transform at least a part of the amorphous silicon film (2) into a polycrystalline silicon film, and an oxidation process for oxidizing the surface of the polycrystalline silicon film in an atmosphere including oxygen, after the irradiation process. Herein, the~~ ~~The~~ laser light (16) is a linear beam having an energy-density gradient of at least 3 (mJ/cm<sup>2</sup>)/μm or more in the a widthwise direction, and the linear beam is generated by transforming ~~pulse pulsed~~ laser light with a wavelength in a range between 350 nm or more and 800 nm or less. The oxidation process is performed in ~~an atmosphere of~~ a saturated water vapor ~~under ambient~~ at a pressure of at least 10 atmospheric pressures or more atmospheres and at a temperature in a range between 500°C or more and 650°C or less. With this method, a semiconductor device with excellent crystallinity can be easily fabricated.